

## NCE N-Channel Enhancement Mode Power MOSFET

## **Description**

The NCE6003XY uses advanced trench technology to provide excellent  $R_{\text{DS}(\text{ON})}$ , low gate charge. This device is suitable for use as a Battery protection or in other switching application.

#### **General Features**

● V<sub>DS</sub> =60V,I<sub>D</sub> =3A

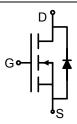
 $R_{DS(ON)}$  <90m $\Omega$  @  $V_{GS}$ =10V

 $R_{DS(ON)}$  < 110m $\Omega$  @  $V_{GS}$ =4.5V

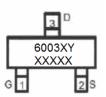
- High power and current handing capability
- Lead free product is acquired
- Surface mount package

## **Application**

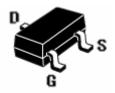
- Battery switch
- ●DC/DC converter



**Schematic Diagram** 



**Marking and Pin Assignment** 



SOT-23-3L Top View

#### **Package Marking and Ordering Information**

Device Marking	Device	Device Package	Reel Size	Tape width	Quantity
6003XY	NCE6003XY	SOT-23-3L	Ø180mm	8 mm	3000 units

#### Absolute Maximum Ratings (T<sub>A</sub>=25℃unless otherwise noted)

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	VDS	60	V
Gate-Source Voltage	V <sub>G</sub> s	±20	V
Drain Current-Continuous	I <sub>D</sub>	3	А
Drain Current-Pulsed (Note 1)	I <sub>DM</sub>	10	Α
Maximum Power Dissipation	P <sub>D</sub>	1.7	W
Operating Junction and Storage Temperature Range	$T_{J}, T_{STG}$	-55 To 150	$^{\circ}$ C

#### **Thermal Characteristic**

Thermal Resistance, Junction-to-Ambient (Note 2)	$R_{\theta,IA}$	73.5	°C/W
	' <b>\</b> UJA	70.0	0,44

#### Electrical Characteristics (T<sub>A</sub>=25°C unless otherwise noted)

Parameter	Symbol	Condition	Min	Тур	Max	Unit	
Off Characteristics							
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	V <sub>GS</sub> =0V I <sub>D</sub> =250μA	60	-	-	V	
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	V <sub>DS</sub> =60V,V <sub>GS</sub> =0V	-	-	1	μΑ	



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# NCE6003XY

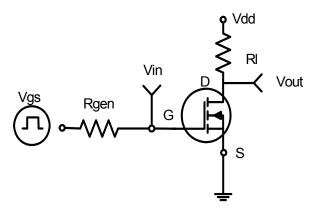
Gate-Body Leakage Current	I <sub>GSS</sub>	V <sub>GS</sub> =±20V,V <sub>DS</sub> =0V	-	-	±100	nA			
On Characteristics (Note 3)									
Gate Threshold Voltage	V <sub>GS(th)</sub>	V <sub>DS</sub> =V <sub>GS</sub> ,I <sub>D</sub> =250μA	0.9	1.3	2.0	V			
Drain-Source On-State Resistance	R <sub>DS(ON)</sub>	V <sub>GS</sub> =10V, I <sub>D</sub> =3A	-	68	90	mΩ			
Diain-Source On-State Resistance		V <sub>GS</sub> =4.5V, I <sub>D</sub> =3A	-	80	110	mΩ			
Forward Transconductance	<b>g</b> FS	V <sub>DS</sub> =5V,I <sub>D</sub> =3A	-	3	-	S			
Dynamic Characteristics (Note4)	·								
Input Capacitance	C <sub>lss</sub>	V <sub>DS</sub> =30V,V <sub>GS</sub> =0V, F=1.0MHz	-	270	-	PF			
Output Capacitance	Coss		-	16	-	PF			
Reverse Transfer Capacitance	C <sub>rss</sub>	F=1.0WHZ	-	15	-	PF			
Switching Characteristics (Note 4)	Switching Characteristics (Note 4)								
Turn-on Delay Time	t <sub>d(on)</sub>	V <sub>DD</sub> =30V,I <sub>D</sub> =3A	-	5	-	nS			
Turn-on Rise Time	t <sub>r</sub>		-	10	-	nS			
Turn-Off Delay Time	t <sub>d(off)</sub>	$V_{GS}$ =10 $V$ , $R_{GEN}$ =1 $\Omega$	-	12	-	nS			
Turn-Off Fall Time	t <sub>f</sub>		-	8	-	nS			
Total Gate Charge	Qg	V <sub>DS</sub> =30V,I <sub>D</sub> =3A, V <sub>GS</sub> =10V	-	10.2	-	nC			
Gate-Source Charge	$Q_{gs}$		-	1.8	-	nC			
Gate-Drain Charge	$Q_{gd}$	V <sub>GS</sub> -10V	-	2.2	-	nC			
Drain-Source Diode Characteristics									
Diode Forward Voltage (Note 3)	V <sub>SD</sub>	V <sub>GS</sub> =0V,I <sub>S</sub> =3A	-	-	1.2	V			
Diode Forward Current (Note 2)	Is		-	-	3	Α			

## Notes:

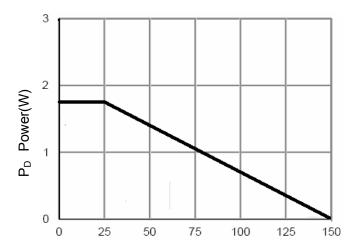
- 1. Repetitive Rating: Pulse width limited by maximum junction temperature.
- Surface Mounted on FR4 Board, t ≤ 10 sec.
   Pulse Test: Pulse Width ≤ 300µs, Duty Cycle ≤ 2%.
- 4. Guaranteed by design, not subject to production



## **Typical Electrical and Thermal Characteristics**



**Figure 1:Switching Test Circuit** 



 $T_J$ -Junction Temperature(°C) Figure 3 Power Dissipation

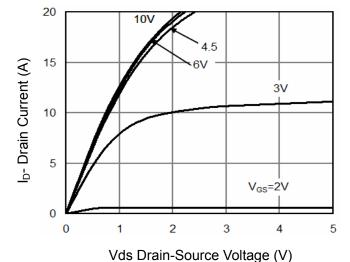
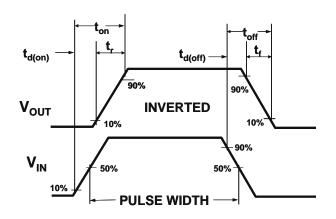
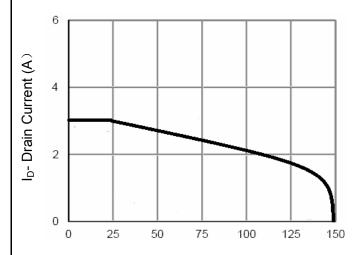


Figure 5 Output Characteristics



**Figure 2:Switching Waveforms** 



T<sub>J</sub>-Junction Temperature(°C)

Figure 4 Drain Current

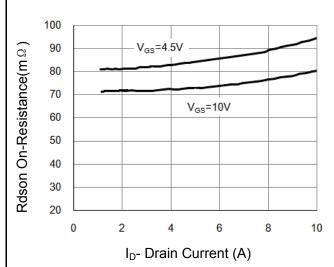
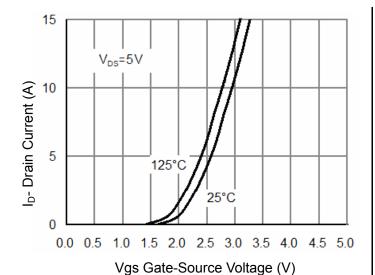
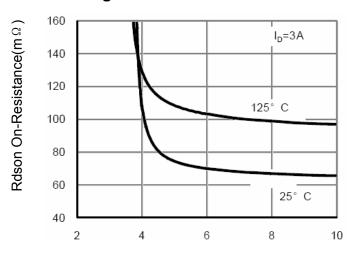


Figure 6 Drain-Source On-Resistance





**Figure 7 Transfer Characteristics** 



Vgs Gate-Source Voltage (V)
Figure 9 Rdson vs Vgs

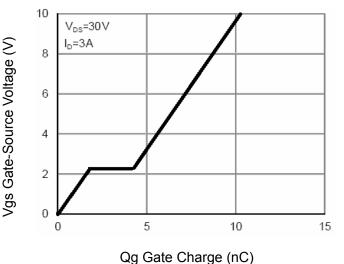


Figure 11 Gate Charge

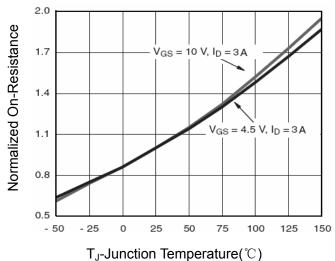


Figure 8 Drain-Source On-Resistance

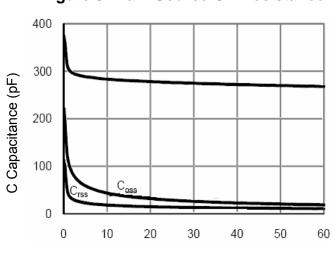


Figure 10 Capacitance vs Vds

Vds Drain-Source Voltage (V)

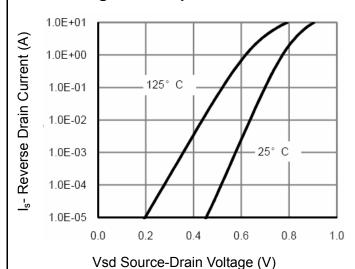
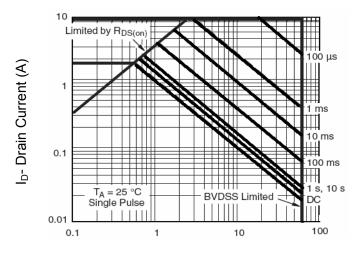


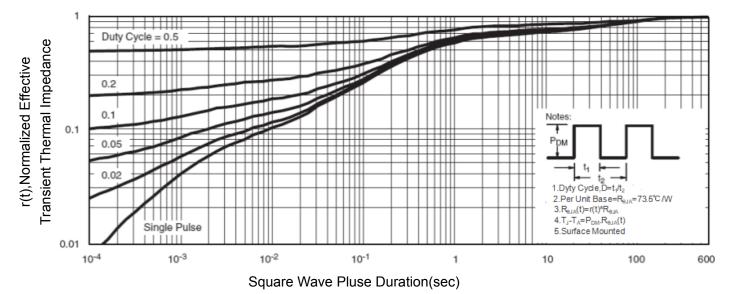
Figure 12 Source- Drain Diode Forward





Vds Drain-Source Voltage (V)

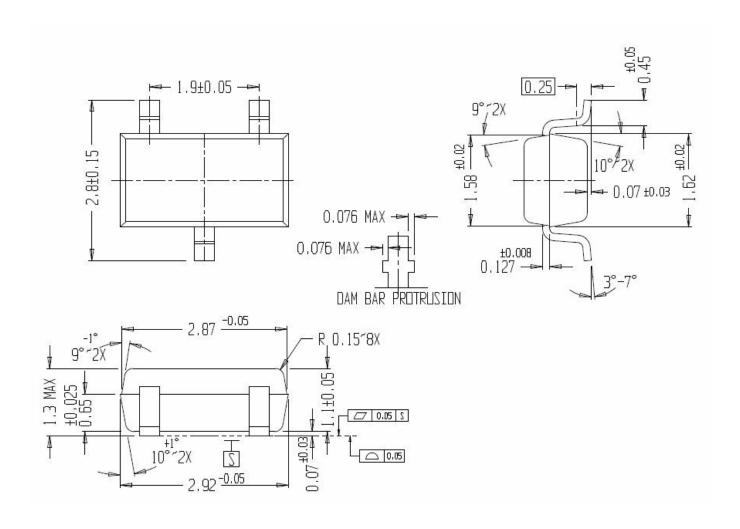
**Figure 13 Safe Operation Area** 



**Figure 14 Normalized Maximum Transient Thermal Impedance** 



## **SOT-23-3L Package Information**



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DMN1017UCP3-7 EFC2J004NUZTDG P85W28HP2F-7071 DMN1053UCP4-7 NTE2384 DMC2700UDMQ-7 DMN2080UCB4-7
DMN61D9UWQ-13 US6M2GTR DMN31D5UDJ-7 DMP22D4UFO-7B IPS60R3K4CEAKMA1 DMN1006UCA6-7 DMN16M9UCA6-7
STF5N65M6 IRF40H233XTMA1 STU5N65M6 DMN6022SSD-13 DMN13M9UCA6-7 DMTH10H4M6SPS-13 IPS60R360PFD7SAKMA1
DMN2990UFB-7B SSM3K35CT,L3F IPLK60R1K0PFD7ATMA1 2N7002W-G MCAC30N06Y-TP IPWS65R035CFD7AXKSA1
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